

Silicon NPN Power Transistors

2SC3047

DESCRIPTION

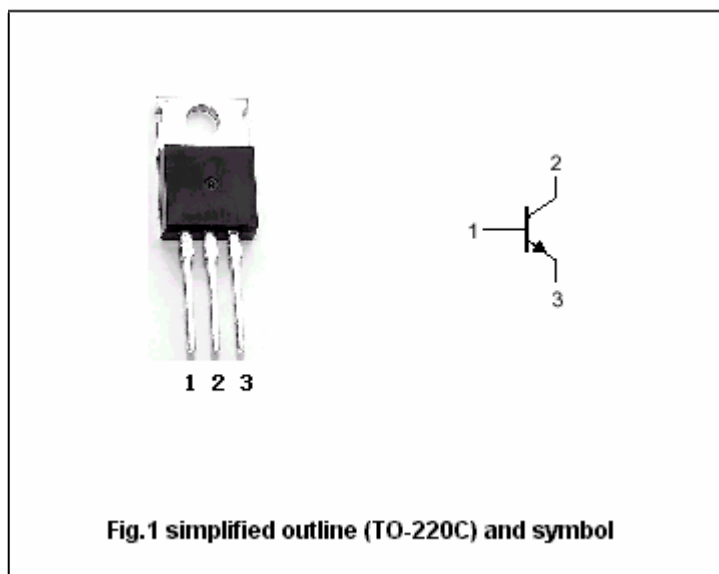
- With TO-220C package
- High voltage ,high speed switching
- High reliability

APPLICATIONS

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	850	V
V_{CEO}	Collector-emitter voltage	Open base	500	V
V_{EBO}	Emitter-base voltage	Open collector	10	V
I_C	Collector current		6	A
I_B	Base current		2	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	40	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-C}$	Thermal resistance junction case	3.0	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA$; $I_B=0$	500			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA$; $I_E=0$	850			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	10			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2A$; $I_B=0.4A$			0.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2A$; $I_B=0.4A$			1.2	V
I_{CBO}	Collector cut-off current	$V_{CB}=850V$; $I_E=0$			1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=10V$; $I_C=0$			1	mA
h_{FE}	DC current gain	$I_C=0.5A$; $V_{CE}=5V$	15			

Switching times

t_{on}	Turn-on time	$I_C=1A$; $I_{B1}=0.1A$ $I_{B2}=-0.2A$; $R_L=300\Omega$			1.0	μs
t_s	Storage time				3.0	μs
t_f	Fall time				1.0	μs

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PACKAGE OUTLINE

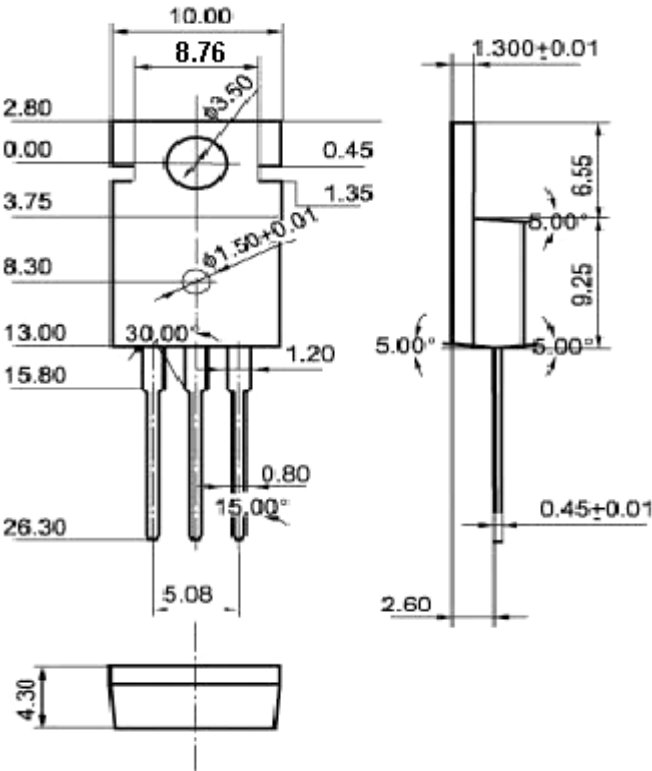


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)